# TOSHIBA

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type ( $L^2-\pi$ -MOSVI)

# 2SJ537

Chopper Regulator, DC-DC Converter and Motor Drive Applications

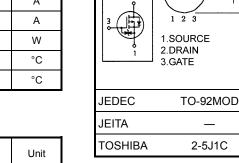
- Low drain-source ON resistance : RDS (ON) = 0.16  $\Omega$  (typ.)
- High forward transfer admittance  $: |Y_{fs}| = 3.5 \text{ S} (typ.)$
- Low leakage current  $: IDSS = -100 \mu A (VDS = -50 V)$
- Enhancement-mode :  $V_{th} = -0.8 \sim -2.0 V (V_{DS} = -10 V, I_D = -1 mA)$ •

### Maximum Ratings (Ta = 25°C)

Characteris	stics	Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	-50	V	
Drain-gate voltage (R <sub>GS</sub> = 20 kΩ)		V <sub>DGR</sub>	-50	V	
Gate-source voltage		V <sub>GSS</sub>	±20	V	
Drain current	DC (Note 1)	Ι <sub>D</sub>	-5	А	
	Pulse (Note 1)	I <sub>DP</sub>	-15	А	
Drain power dissipation		PD	0.9	W	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	

## **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	R <sub>th (ch−a)</sub>	138	°C / W



Weight: 0.36 g (typ.)

Note 1: Please use devices on condition that the channel temperature is below 150°C.

This transistor is an electrostatic sensitive device. Please handle with caution.

2.2 max 8.2

1.27 ).6 max min

10.5

max

5.1 max

0.75 max 1.0 max

0.8 max 0.6 max

1.27

2 54

Unit: mm

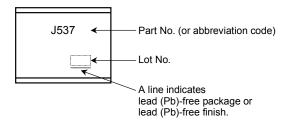
## Electrical Characteristics (Ta = 25°C)

Charao	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cu	urrent	I <sub>GSS</sub>	V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0 V		—	±10	μA	
Drain cut-off cu	rrent	I <sub>DSS</sub>	$V_{DS}$ = -50 V, $V_{GS}$ = 0 V		_	-100	μA	
Drain-source br voltage	eakdown	V (BR) DSS	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0 V	-50	_	_	V	
Gate threshold	voltage	V <sub>th</sub>	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -1 \text{ mA}$	-0.8	_	-2.0	V	
Drain-source ON resistance		R <sub>DS (ON)</sub>	V <sub>GS</sub> = -4 V, I <sub>D</sub> = -1.3 A	_	0.27	0.34	Ω	
			V <sub>GS</sub> = -10 V, I <sub>D</sub> = -2.5 A	_	0.16	0.19		
Forward transfe	r admittance	Y <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -2.5 A	1.5	3.5	_	S	
Input capacitant	ce	C <sub>iss</sub>			470	_		
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz		60	_	pF	
Output capacitance		C <sub>oss</sub>			210	_		
Switching time	Rise time	tr	$V_{GS} \xrightarrow{0V} I_{D} \xrightarrow{I_{D} = -2.5A} V_{OUT}$	_	25	_	ns	
	Turn-on time	t <sub>on</sub>		_	35	_		
	Fall time	t <sub>f</sub>		_	20	_		
	Turn-off time	t <sub>off</sub>	$V_{DD} = -25V$ Duty $\leq 1\%$ , t <sub>w</sub> = 10 $\mu$ s	_	120	_		
Total gate charge (Gate-source plus gate-drain)		Qg	_ V <sub>DD</sub> ≈ −40 V, V <sub>GS</sub> = −10 V,	_	18	_	nC	
Gate-source charge		Q <sub>gs</sub>	$I_{\rm D} = -5 {\rm A}$	_	13	_		
Gate-drain ("miller") charge		Q <sub>gd</sub>		_	5	_		

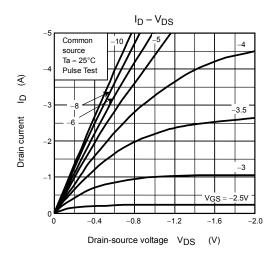
## Source-Drain Ratings and Characteristics (Ta = 25°C)

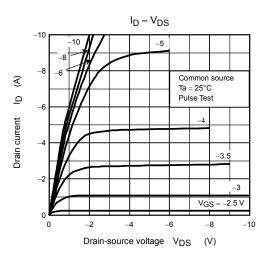
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	—		_	-5	А
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	_	Ι	_	-15	А
Forward voltage (diode)	V <sub>DSF</sub>	$I_{DR} = -5 \text{ A}, \text{ V}_{GS} = 0 \text{ V}$	_		1.5	V

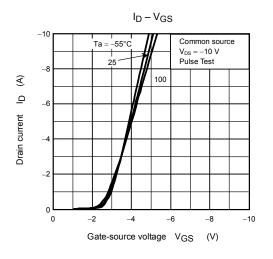
## Marking

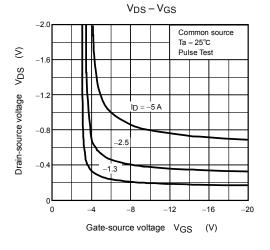


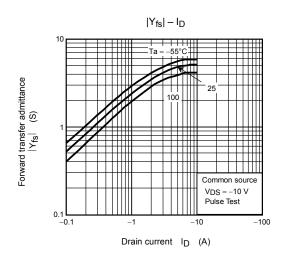
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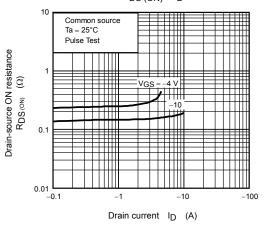


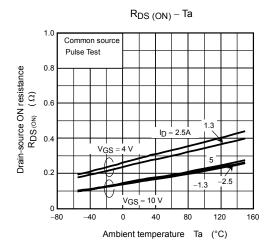


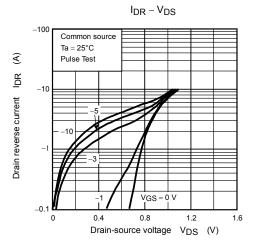


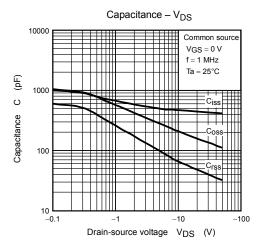


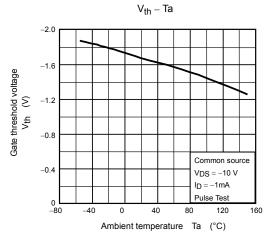
 $R_{DS(ON)} - I_D$ 



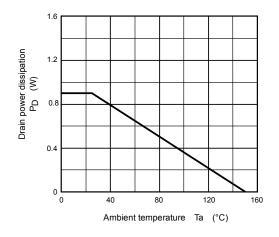


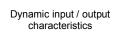


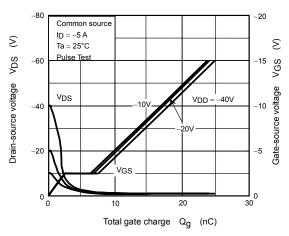


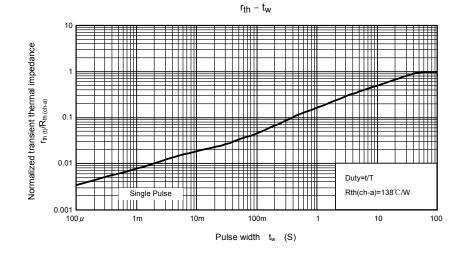


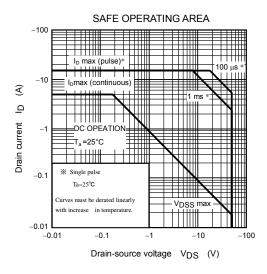












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